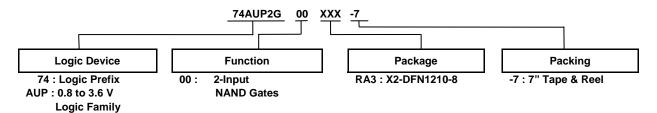


Ordering Information

2G: Dual Gate



	Package	Package	Package	7" Tape and Reel		
Device	Code (Notes 4 & 5)	Size	Quantity	Part Number Suffix		
74AUP2G00RA3-7	RA3	X2-DFN1210-8	1.2mm X 1.0mm X 0.35mm 0.3 mm lead pitch	5,000/Tape & Reel	-7	

Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

5. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.

Pin Descriptions

Pin Name	Pin No.	Function					
1A	1	Data Input					
1B	2	Data Input					
2Y	3	Data Output					
GND	4	Ground					
2A	5	Data Input					
2B	6	Data Input					
1Y	7	Data Output					
V _{CC}	8	Supply Voltage					

Logic Diagram

Function Table

Inp	uts	Output			
Α	В	Υ			
L	L	Н			
L	Н	Н			
Н	L	Н			
Н	Н	L			



Absolute Maximum Ratings (Note 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to +4.6	V
Vı	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V _{CC} +0.5	V
lık	Input Clamp Current V _I <0	50	mA
I _{OK}	Output Clamp Current (V _O < 0)	50	mA
Io	Continuous Output Current (V _O = 0 to V _{CC})	±20	mA
Icc	Continuous Current Through V _{CC}	50	mA
I _{GND}	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes:

Recommended Operating Conditions (Note 8)

Symbol	Pa	arameter	Min	Max	Unit
V _{CC}	Operating Voltage	_	0.8	3.6	V
VI	Input Voltage		0	3.6	V
Vo	Output Voltage	Output Voltage			
		V _{CC} = 0.8V	_	-20	μΑ
		V _{CC} = 1.1V	_	-1.1	
	Library Contract Contract	V _{CC} = 1.4V	_	-1.7	
I _{OH}	High-Level Output Current	V _{CC} = 1.65V	_	-1.9	mA
		V _{CC} = 2.3V	_	-3.1	
		V _{CC} = 3.0V	_	-4	
		V _{CC} = 0.8V	_	20	μΑ
		V _{CC} = 1.1V	_	1.1	
		V _{CC} = 1.4V	_	1.7	
I _{OL}	Low-Level Output Current	V _{CC} = 1.65V	_	1.9	mA
		V _{CC} = 2.3V	_	3.1	
		V _{CC} = 3.0V	_	4	
Δt/ΔV	Input Transition Rise or Fall Rate	V _{CC} = 0.8V to 3.6V	_	200	ns/V
T _A	Operating Free-Air Temperature	_	-40	+125	°C

Note: 8. Unused inputs should be held at V_{CC} or Ground.

^{6.} Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device

operation should be within recommended values.

7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely, forcing the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.



Electrical Characteristics

Symbol	Parameter	Test Conditions	Voc	T _A = -	+25°C	$T_A = -40^{\circ}C$	C to +85°C	Unit
Syllibol	Parameter	rest Conditions	V _{CC}	Min	Max	Min	Max	Onit
		_	0.8V to 1.65V	0.80 X V _{CC}	_	0.80 X V _{CC}	_	
V _{IH}	High-Level Input	_	1.65V to 1.95V	0.65 X V _{CC}	_	0.65 X V _{CC}	_	V
VIH	Voltage	_	2.3V to 2.7V	1.6	_	1.6	_	ľ
			3.0V to 3.6V	2.0	_	2.0	_	
		_	0.8V to 1.65V	_	0.30 X V _{CC}	_	0.30 X V _{CC}	
VIL	Low-Level Input	_	1.65V to 1.95V	_	0.35 X V _{CC}	_	0.35 X V _{CC}	V
VIL	Voltage	_	2.3V to 2.7V	_	0.7	_	0.7	•
		_	3.0V to 3.6V	_	0.9	_	0.9	
		$I_{OH} = -20 \mu A$	0.8V to 3.6V	V _{CC} – 0.1	_	V _{CC} – 0.1	_	
		I _{OH} = -1.1mA	1.1V	0.75 X V _{CC}	_	0.7 X V _{CC}	_	
		$I_{OH} = -1.7 \text{mA}$	1.4V	1.11	_	1.03	_	
V _{OH}	High-Level Output	$I_{OH} = -1.9 \text{mA}$	1.65V	1.32	_	1.3	_	V
VOH	Voltage	I_{OH} = -2.3mA	2.3V	2.05	_	1.97	_	V
		I _{OH} = -3.1mA	2.30	1.9	_	1.85	_	
		I _{OH} = -2.7mA	3V	2.72	_	2.67	_	
		I _{OH} = -4mA	30	2.6	_	2.55	_	
		I _{OL} = 20μA	0.8V to 3.6V	_	0.1	_	0.1	
		I _{OL} = 1.1mA	1.1V	_	0.3 X V _{CC}	_	0.3 X V _{CC}	
		I _{OL} = 1.7mA	1.4V	_	0.31	_	0.37	
.,	Low-Level Input	I _{OL} = 1.9mA	1.65V	_	0.31	_	0.35	V
V_{OL}	Voltage	I _{OL} = 2.3mA	0.01/	_	0.31	_	0.33	V
		I _{OL} = 3.1mA	2.3V	_	0.44	_	0.45	
		I _{OL} = 2.7mA	0) (_	0.31	_	0.33	
		I _{OL} = 4mA	3V	_	0.44	_	0.45	
II	Input Current	A or B Input V _I = GND to 3.6V	0V to 3.6V	_	± 0.1	_	± 0.5	μΑ
l _{OFF}	Power Down Leakage Current	V_I or $V_O = 0V$ to 3.6V	0V	_	± 0.2	_	± 0.6	μA
Δl _{OFF}	Delta Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0V to 0.2V	_	± 0.2	_	± 0.6	μA
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	0.5	_	0.9	μΑ
Δl _{CC}	Additional Supply Current	One Input at V _{CC} –0.6V Other Inputs at V _{CC} or GND	3.3V	_	40	_	50	μA



Electrical Characteristics (continued)

Symbol	Parameter	Test Conditions	V	T _A = -40°C	to +125°C	Unit
Symbol	Parameter	rest Conditions	V _{CC}	Min	Max	Unit
		_	0.8V to 1.65V	0.80 X V _{CC}	_	
V _{IH}	High-Level Input Voltage	_	1.65V to 1.95V	0.70 X V _{CC}	_	V
VIH	Triigh-Level input voltage	_	2.3V to 2.7V	1.6	_	v
		_	3.0V to 3.6V	2.0	_	
		_	0.8V to 1.65V	_	0.25 X V _{CC}	
V_{IL}	Low-Level Input Voltage	_	1.65V to 1.95V		0.30 X V _{CC}	V
VIL	Low Level input voltage	_	2.3V to 2.7V	_	0.7	·
		_	3.0V to 3.6V		0.9	
		$I_{OH} = -20\mu A$	0.8V to 3.6V	V _{CC} – 0.11	_	
		$I_{OH} = -1.1$ mA	1.1V	0.6 X V _{CC}	_	
		I _{OH} = -1.7mA	1.4V	0.93	_	
., .	High Lavel Output Valters	I _{OH} = -1.9mA	1.65V	1.17	_	.,
Vон	High-Level Output Voltage	I _{OH} = -2.3mA	2.21/	1.77	_	V
		I _{OH} = -3.1mA	2.3V	1.67	_	
		I _{OH} = -2.7mA	21/	2.40	_	
		I _{OH} = -4mA	3V	2.30	_	
		I _{OL} = 20μA	0.8V to 3.6V	_	0.11	
		I _{OL} = 1.1mA	1.1V	_	0.33 X V _{CC}	
		I _{OL} = 1.7mA	1.4V	_	0.41	
.,	Lava Lava Harrist Walterna	I _{OL} = 1.9mA	1.65V	_	0.39	.,
V _{OL}	Low-Level Input Voltage	I _{OL} = 2.3mA	0.01/	_	0.36	V
		I _{OL} = 3.1mA	2.3V	_	0.50	
		I _{OL} = 2.7mA	01/	_	0.36	
		I _{OL} = 4mA	3V	_	0.50	
l _l	Input Current	A or B Input, V _I = GND to 3.6V	0V to 3.6V	_	± 0.75	μA
l _{OFF}	Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0V	_	± 1.0	μA
Δl _{OFF}	Delta Power Down Leakage Current	V_I or $V_O = 0V$ to 3.6V	0V to 0.2V	_	± 2.5	μA
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	3.0	μA
Δl _{CC}	Additional Supply Current	Input at V _{CC} –0.6V Other Inputs at V _{CC} or GND	3.3V	_	75	μΑ

Operating and Package Characteristics (@T_A = +25°C, unless otherwise specified.)

	Parameter	Te: Condi		V _{CC}	Тур	Unit
				0.8V	5.1	
	C _{pd} Power Dissipation Capacitance			1.2V ± 0.1V	5.2	
0		f = 1N	ИНz	1.5V ± 0.1V	5.2	٦
$C_{\sf pd}$		No L	oad	1.8V ± 0.15V	5.5	pF
				2.5V ± 0.2V	5.7	
				3.3V ± 0.3V	6.0	
Ci	Input Capacitance	$V_i = V_{CC}$	or GND	0V or 3.3V	2.0	pF
θ_{JA}	Thermal Resistance Junction-to-Ambient	X2-DFN1210-8	X2-DFN1210-8 (Note 9)		395	°C/W
θ_{JC}	Thermal Resistance Junction-to-Case	X2-DFN1210-8	(Note 9)	_	236	°C/W

Note: 9. Test condition, X2-DFN1210-8 device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Switching Characteristics

C_L=5pF, See Figure 1

Parameter	From	то	V	T	T _A = +25°C		T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
Faranietei	Input OUTPUT	Vcc	Min	Тур	Max	Min	Max	Min	Max	Oiiit	
			0.8V	_	20.1	_	_	_	_	_	
			1.2V ± 0.1V	2.5	5.3	12.1	2.1	13.4	2.1	14.9	
_			1.5V ± 0.1V	2.0	3.8	6.8	1.8	7.8	1.8	8.6	
Грd	t _{pd} A Y	Ť	1.8V ± 0.15V	1.6	3.1	5.3	1.4	6.2	1.4	6.9	ns
			2.5V ± 0.2V	1.3	2.5	4.0	1.1	4.7	1.1	5.2	1
			3.3V ± 0.3V	1.0	2.2	3.6	1.0	4.2	1.0	4.7	

C_L= 10pF, See Figure 1

Parameter	From	то	V	Т	T _A = +25°C		T _A = -40°C to +85°C		T _A = -40°C	to +125°C	Unit
Parameter	Input	OUTPUT	V _{CC}	Min	Тур	Max	Min	Max	Min	Max	Oilit
			V8.0	_	24.2	_	_	_	_	_	
			1.2V ± 0.1V	2.4	6.1	14.3	2.2	15.8	2.2	17.5	
		V	1.5V ± 0.1V	2.4	4.4	7.9	2.2	9.2	2.2	10.2	ns
t _{pd}	Α	ı	1.8V ± 0.15V	2.0	3.7	6.2	1.9	7.3	1.9	8.1	
			2.5V ± 0.2V	1.4	3.0	4.7	1.3	5.6	1.3	6.2	
			$3.3V \pm 0.3V$	1.3	2.8	4.3	1.2	4.9	1.2	5.4	

C_L = 15pF, See Figure 1

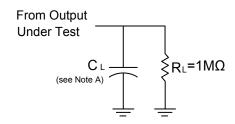
Parameter	From	то	.,	T _A = +25°C			T _A = -40°C to +85°C		$T_A = -40^{\circ}C \text{ to } +125^{\circ}C$		Unit
	Input	OUTPUT	Vcc	Min	Тур	Max	Min	Max	Min	Max	Unit
		0.8V	_	28.2	_	_	_	_	_		
			1.2V ± 0.1V	3.4	6.9	16.3	3.1	20.3	3.1	20.5	_
	^		1.5V ± 0.1V	2.8	5.0	8.9	2.5	10.5	2.5	11.6	
t _{pd}	Α	Ţ	1.8V ± 0.15V	2.0	4.1	7.0	2.0	8.3	2.0	9.2	ns
		2.5V ± 0.2V	1.7	3.5	5.3	1.5	6.4	1.5	7.1	1	
			$3.3V \pm 0.3V$	1.4	3.2	4.9	1.3	5.7	1.3	6.3	

C_L = 30pF, See Figure 1

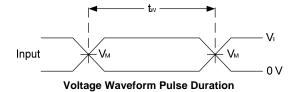
Parameter	From	то	V	Т	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C	
Faranietei	Input OUTPUT	V _{CC}	Min	Тур	Min	Min	Max	Min	Max	Unit	
			V8.0	_	40.0	_	_	_	_	_	
			1.2V ± 0.1V	4.6	9.2	22.1	4.1	27.8	4.1	28.0	ns
	۸		1.5V ± 0.1V	3.0	6.5	11.8	2.9	14.0	2.9	15.4	
t _{pd}	AY	ı	1.8V ± 0.15V	2.6	5.4	9.3	2.3	11.1	2.3	12.3	
		2.5V ± 0.2V	2.4	4.6	7.1	2.1	8.5	2.1	9.4	1	
			3.3V ± 0.3V	2.0	4.3	6.5	1.8	7.6	1.8	8.4	

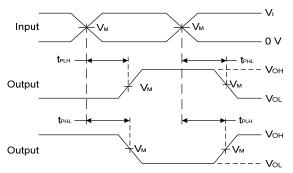


Parameter Measurement Information



Vcc	Inputs		.,	•
	VI	t _r /t _f	V _M	C _L
0.8V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.2V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.5V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.8V ± 0.15V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
2.5V ± 0.2V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
3.3V ± 0.3V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF





Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1 Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
 C. Inputs are measured separately one transition per measurement.
- D. t_{PLH} and t_{PHL} are the same as $t_{\text{PD.}}$



Marking Information

X2-DFN1210-8

(Top View)

 $\underline{XX}\,$: Identification Code

<u>Y</u> : Year : 0~9

 $\overline{\underline{W}}$: week: A~Z: 1~26 week

a~z: 27-52 week

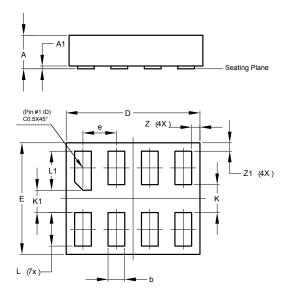
z represents 52 and 53 week

 \underline{X} : week: A~Z: Internal code

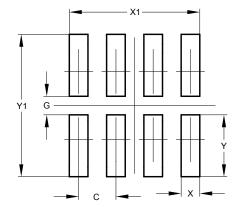
Part Number	Package	Identification Code	
74AUP2G00RA3-7	X2-DFN1210-8	AT	

X2-DFN1210-8 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X2-DFN1210-8				
Dim	Min	Max	Тур	
Α	-	0.35	0.30	
A 1	0	0.03	0.02	
b	0.10	0.20	0.15	
D	1.15	1.25	1.20	
E	0.95	1.05	1.00	
е	-	-	0.30	
K	-	-	0.25	
K1	-	-	0.20	
L	0.25	0.35	0.30	
L1	0.30	0.40	0.35	
Z	0.050	0.100	0.075	
Z 1	0.050	0.100	0.075	
All Dimensions in mm				



Dimensions	Value (in mm)	
С	0.300	
G	0.150	
Х	0.150	
X1	1.050	
Y	0.500	
Y1	1.150	



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.

Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2015, Diodes Incorporated

www.diodes.com